

# 3 A low V<sub>F</sub> MEGA Schottky barrier rectifier Rev. 01 — 27 October 2009

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

### 1.2 Features

- Average forward current:  $I_{F(AV)} \le 3 A$
- Reverse voltage:  $V_R \le 30 \text{ V}$
- Low forward voltage
- High power capability due to clip-bond technology
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

### 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

### 1.4 Quick reference data

#### Table 1. Quick reference data

 $T_i = 25 \circ C$  unless otherwise specified.

)	I					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	square wave; $\delta = 0.5;$ f = 20 kHz				
		$T_{amb} \le 70 \ ^{\circ}C$	<u>[1]</u> _	-	3	А
		$T_{sp} \le 140 \ ^{\circ}C$	-	-	3	А
V <sub>R</sub>	reverse voltage		-	-	30	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 3 A	-	400	450	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 30 V	-	55	150	μΑ

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



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### 2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	84
2	anode	1	1 1 2
			sym001

[1] The marking bar indicates the cathode.

### 3. Ordering information

Table 3. Order	ing inform	ation	
Type number	Package		
	Name	Description	Version
PMEG3030BEP	-	plastic surface-mounted package; 2 leads	SOD128

### 4. Marking

Table 4.	Marking codes	
Type numbe	er	Marking code
PMEG3030E	3EP	A6

### 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

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Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C	-	30	V
I <sub>F(AV)</sub>	average forward current	square wave; $\delta$ = 0.5; f = 20 kHz			
		$T_{amb} \le 70 \ ^{\circ}C$	<u>[1]</u> _	3	А
		$T_{sp} \le 140 \ ^{\circ}C$	-	3	А
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; t <sub>p</sub> = 8 ms	[2] _	50	А
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[3][4] _	625	mW
			[3][5]	1050	mW
			[3][1]	2100	mW

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#### Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Т <sub>ј</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on a ceramic PCB,  $AI_2O_3$ , standard footprint.

[2]  $T_j = 25 \ ^{\circ}C$  prior to surge.

[3] Reflow soldering is the only recommended soldering method.

- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1][2]			
	junction to ambient		[3] _	-	200	K/W
			[4] _	-	120	K/W
			[5] _	-	60	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		<u>[6]</u> _	-	12	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses  $P_R$  are a significant part of the total power losses.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

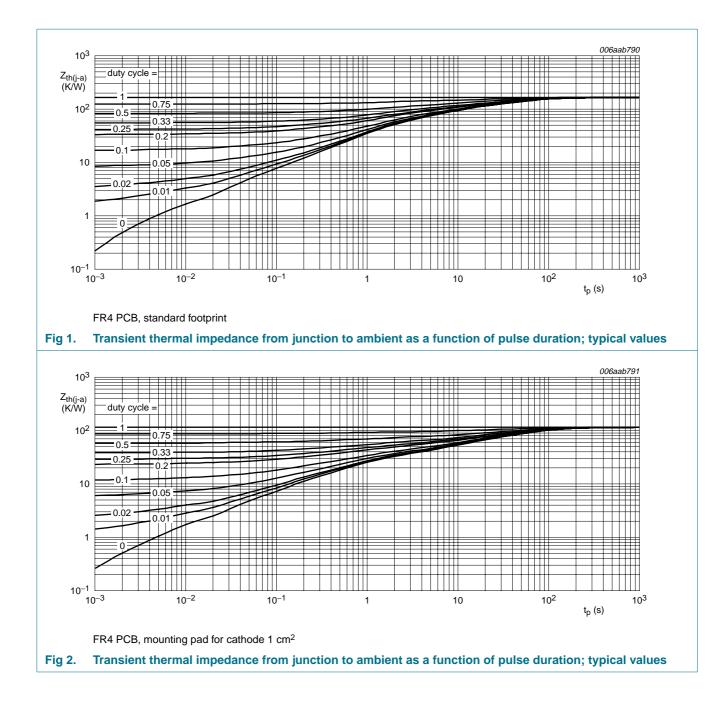
[5] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.

[6] Soldering point of cathode tab.

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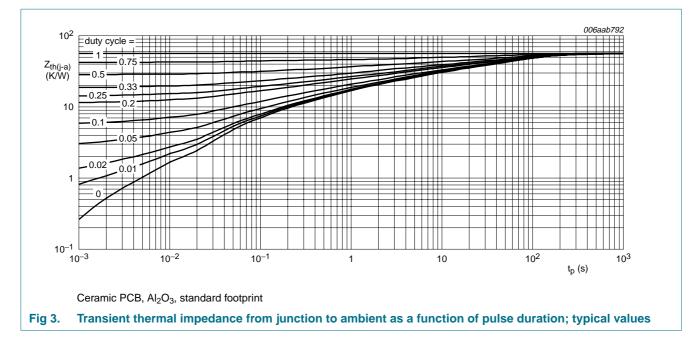
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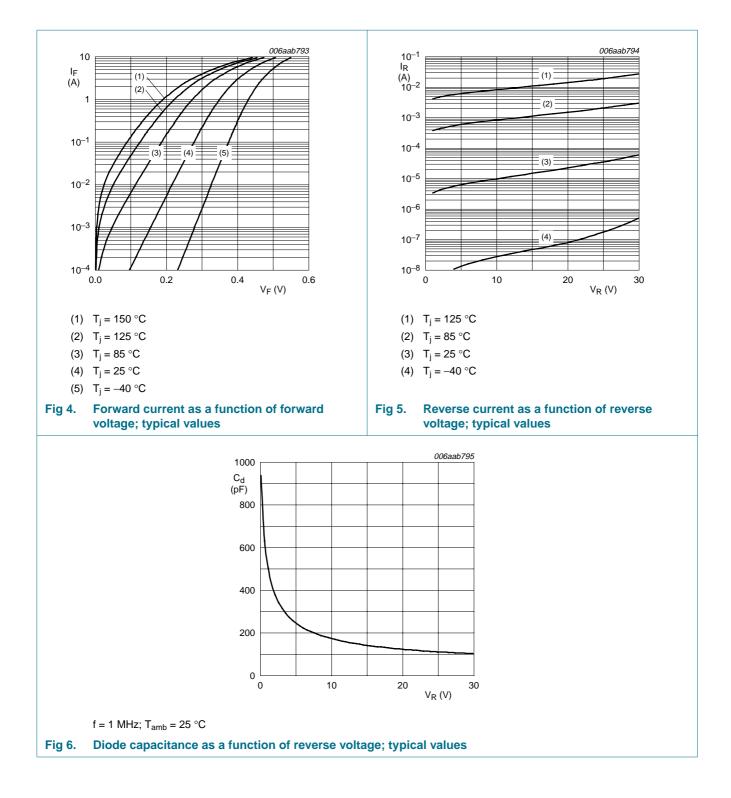
#### 3 A low V<sub>F</sub> MEGA Schottky barrier rectifier

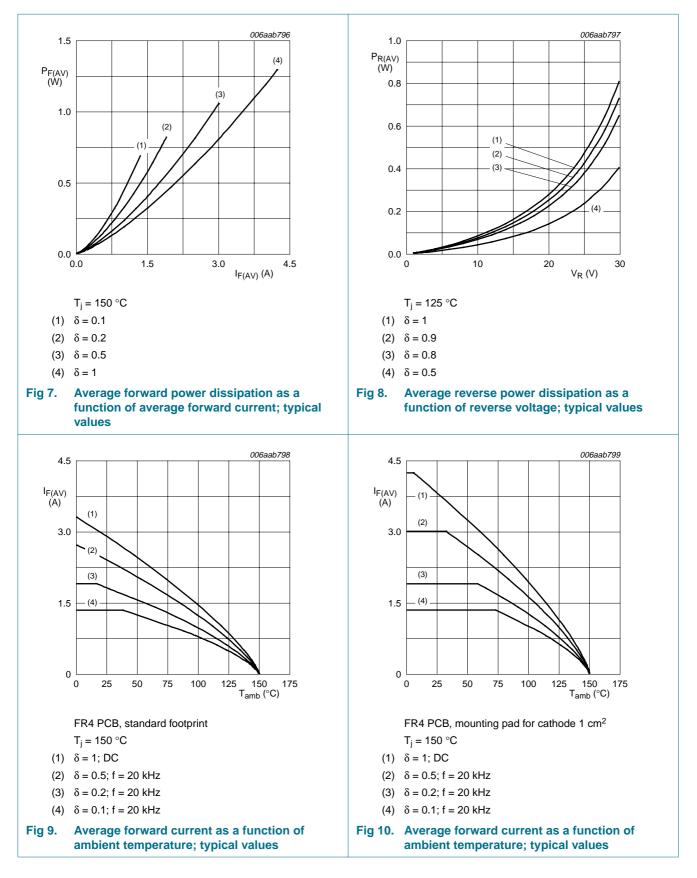


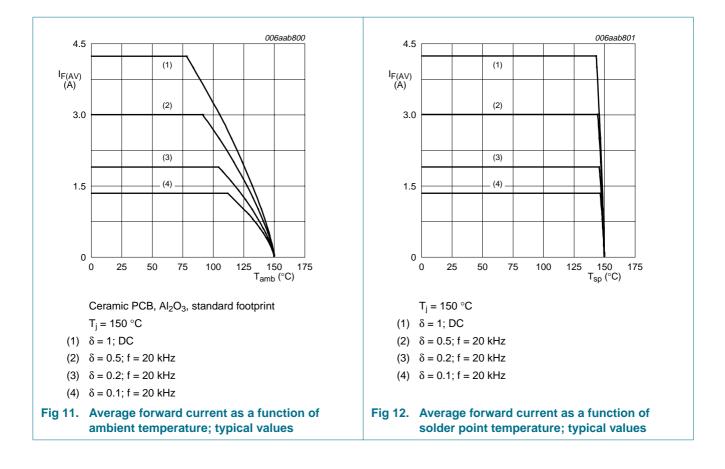
### 7. Characteristics

Table 7.Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 0.1 A	-	280	320	mV
		I <sub>F</sub> = 0.5 A	-	330	380	mV
		I <sub>F</sub> = 1 A	-	350	400	mV
		I <sub>F</sub> = 1.5 A	-	365	420	mV
		I <sub>F</sub> = 2 A	-	380	440	mV
		I <sub>F</sub> = 3 A	-	400	450	mV
I <sub>R</sub> reverse curre	reverse current	$V_R = 5 V$	-	6	-	μA
		V <sub>R</sub> = 10 V	-	9	-	μΑ
		V <sub>R</sub> = 30 V	-	55	150	μΑ
C <sub>d</sub>	diode capacitance	f = 1 MHz				
		$V_R = 1 V$	-	500	-	pF
		V <sub>R</sub> = 10 V	-	170	-	рF

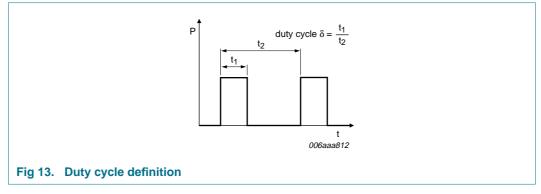






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### 8. Test information

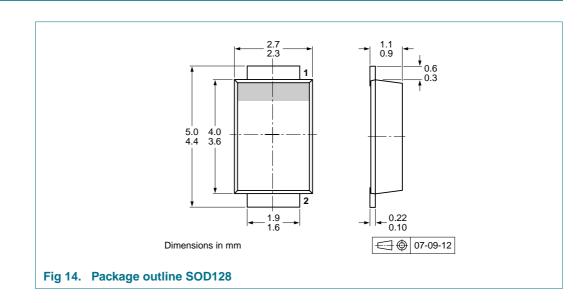


The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,

 $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.



### 9. Package outline

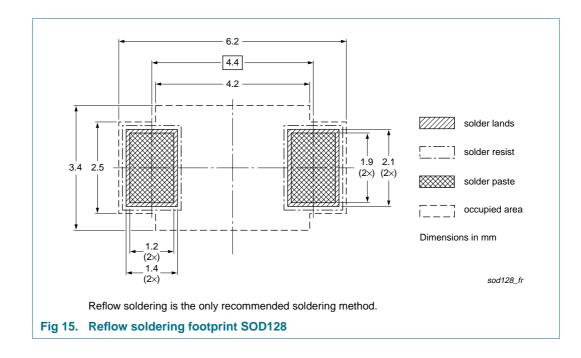
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### **10. Packing information**

	i <mark>ng methods</mark> x are the last	t three digits of the 12NC ordering code.[1]	
Type number         Package         Description         Packing quantity			
			3000
PMEG3030BEP	SOD128	4 mm pitch, 12 mm tape and reel	-115
[1] For further info	rmation and th	ne availability of packing methods, see Section 14.	

### **11. Soldering**



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## **12. Revision history**

Table 9. Revision hist	Revision history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3030BEP_1	20091027	Product data sheet	-	-

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### **13. Legal information**

### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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